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# ACTT4X-800E

## AC Thyristor Triac power switch

15 August 2014

Product data sheet

## 1. General description

Planar passivated AC Thyristor Triac power switch in a SOT186A (TO-220F) "full pack" plastic package with self-protective capabilities against low and high energy transients.

## 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Direct interfacing with low power drivers and microcontrollers
- Full cycle AC conduction
- Isolated mounting base package
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Safe clamping capability for low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

## 3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	-	800	V
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(Init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	35	A
$T_{\text{j}}$	junction temperature		-	-	125	$^{\circ}\text{C}$
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{h}} \leq 94\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	4	A



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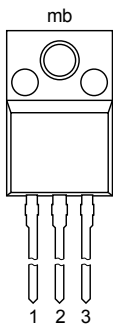
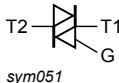
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{PP}$	peak pulse voltage	$T_j = 25\text{ }^{\circ}\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>	-	-	2	kV
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 8</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 8</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 8</a>	-	-	10	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25\text{ }^{\circ}\text{C}$	850	-	-	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^{\circ}\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 13</a>	500	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^{\circ}\text{C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	8	-	-	A/ms

## 5. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-220F (SOT186A)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
ACTT4X-800E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

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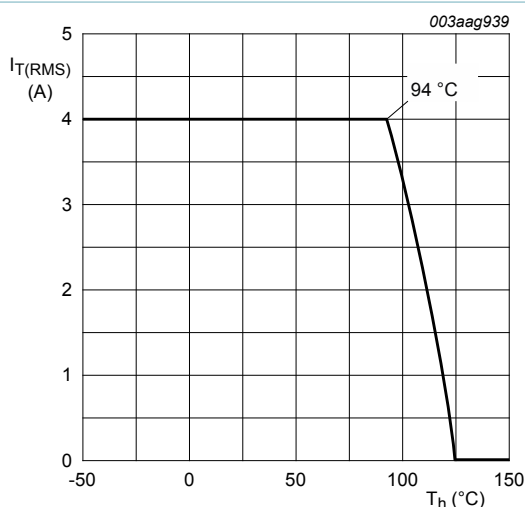
### AC Thyristor Triac power switch

## 7. Limiting values

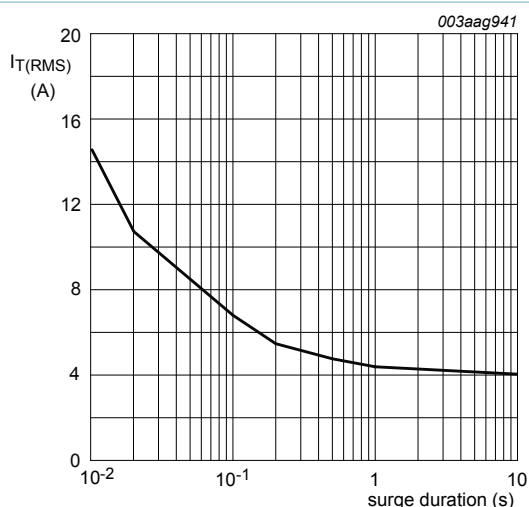
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_h \leq 94^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	4	A
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25^\circ\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	35	A
		full sine wave; $T_{\text{j(init)}} = 25^\circ\text{C}$ ; $t_p = 16.7\text{ ms}$	-	39	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	6	$\text{A}^2\text{s}$
$di_{\text{T}}/dt$	rate of rise of on-state current	$I_{\text{T}} = 6\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
$I_{\text{GM}}$	peak gate current	$t = 20\text{ }\mu\text{s}$	-	2	A
$P_{\text{GM}}$	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
$T_{\text{stg}}$	storage temperature		-40	150	$^\circ\text{C}$
$T_{\text{j}}$	junction temperature		-	125	$^\circ\text{C}$
$V_{\text{PP}}$	peak pulse voltage	$T_{\text{j}} = 25^\circ\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>	-	2	kV



**Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values**



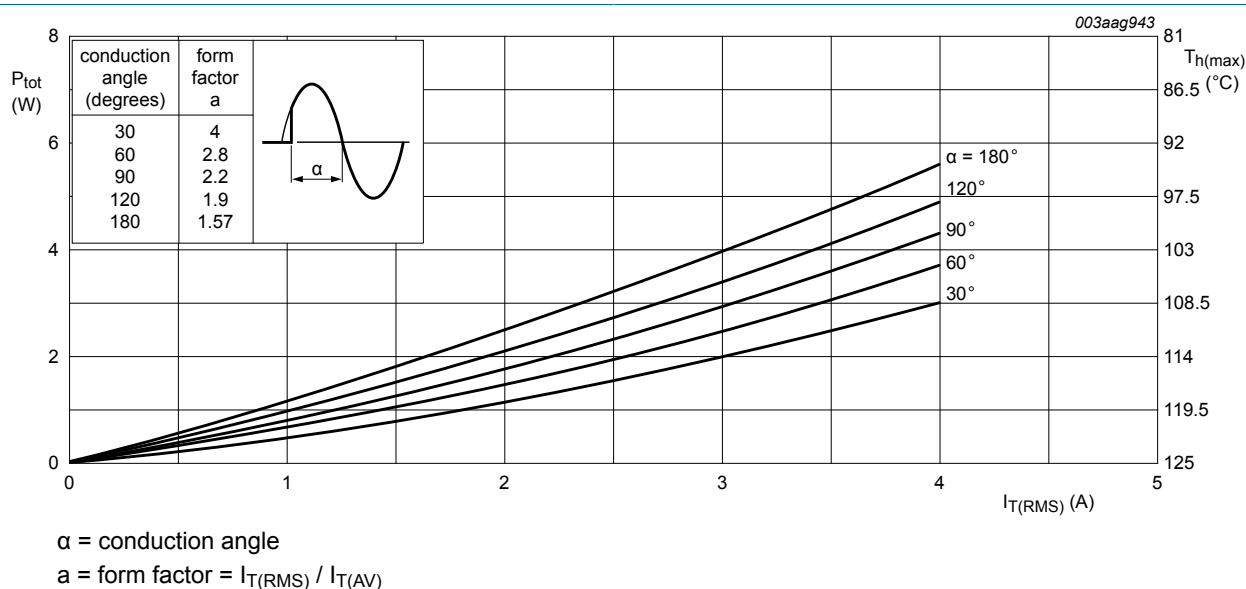
$f = 50\text{ Hz}$ ;  $T_h = 94^\circ\text{C}$

**Fig. 2. on-state current as a function of surge duration; maximum values**

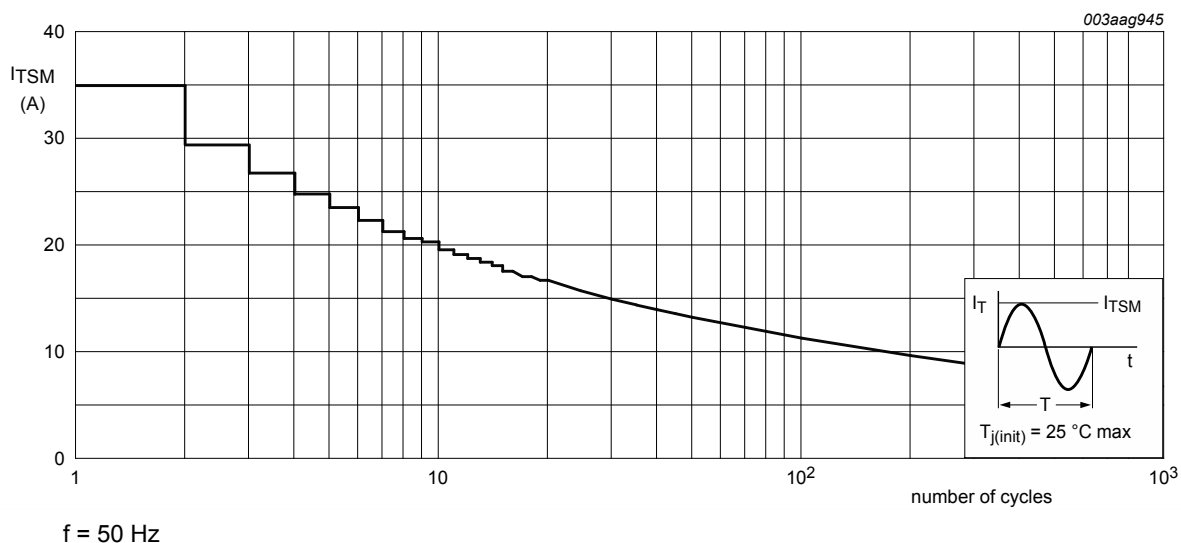
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**Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values**

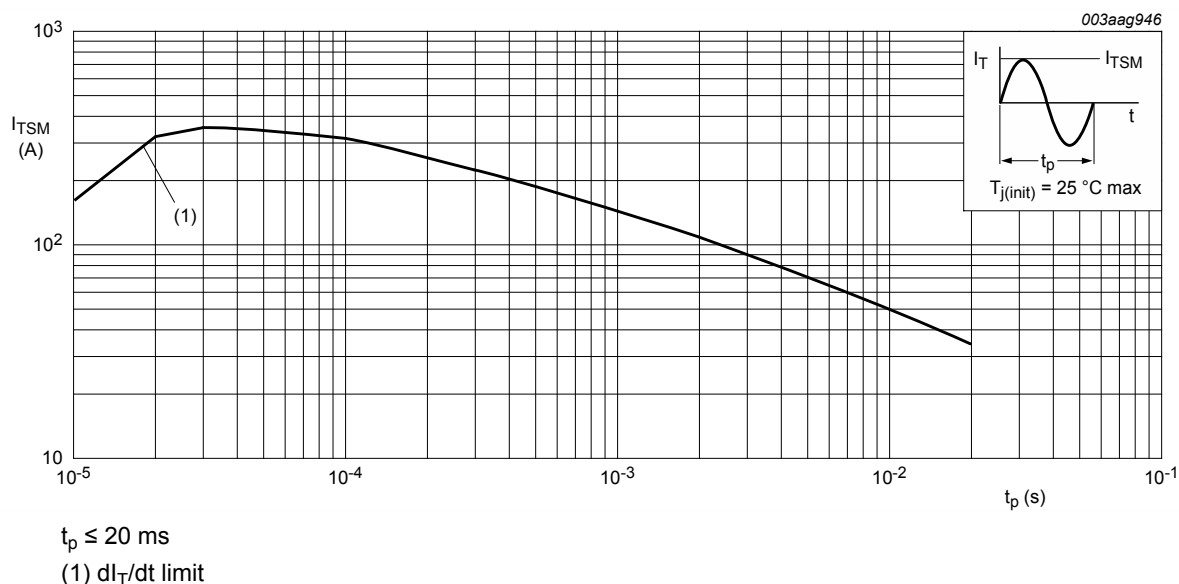


**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**

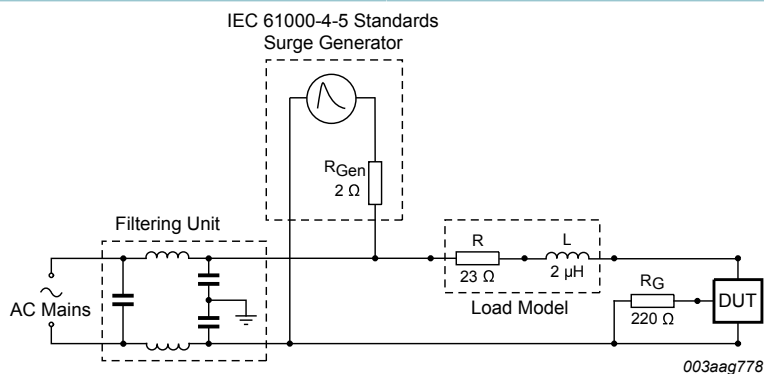
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**Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values**



**Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5**

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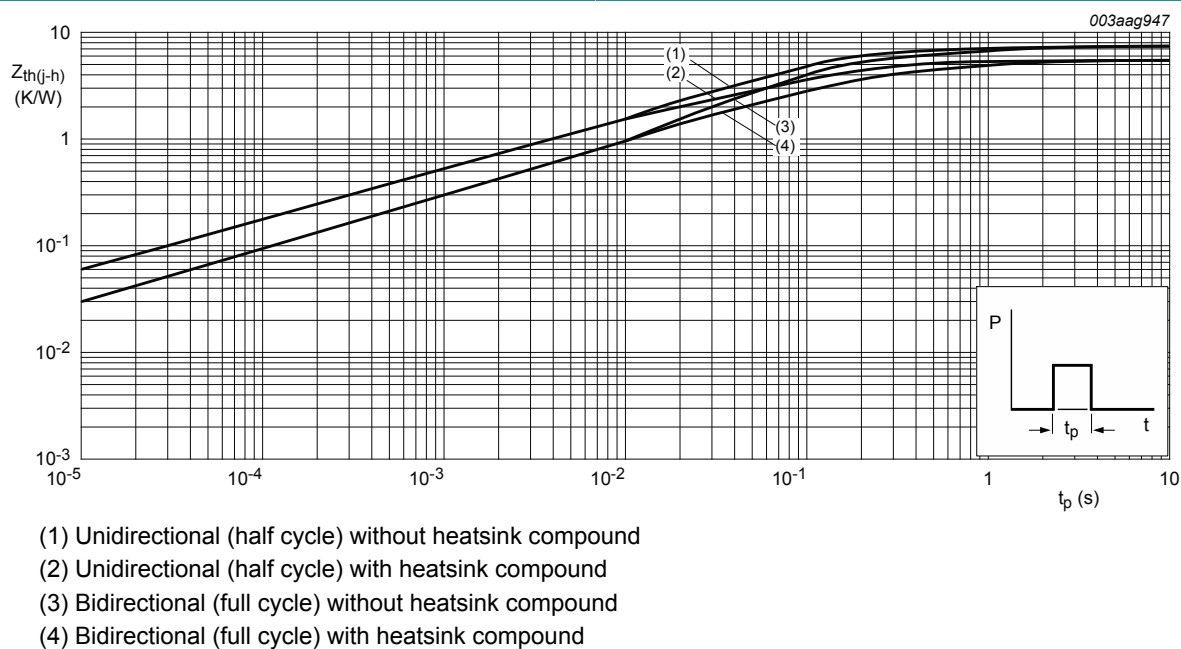
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## 8. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; <a href="#">Fig. 7</a>	-	-	5.5	K/W
		full cycle or half cycle; without heatsink compound; <a href="#">Fig. 7</a>	-	-	7.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



**Fig. 7. Transient thermal impedance from junction to heatsink as a function of pulse width**

## 9. Isolation characteristics

**Table 6. Isolation characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65% RH; T <sub>h</sub> = 25 °C; from all terminals to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
$C_{isol}$	isolation capacitance	f = 1 MHz; T <sub>h</sub> = 25 °C; from main terminal 2 to external heatsink	-	10	-	pF

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## 10. Characteristics

Table 7. Characteristics

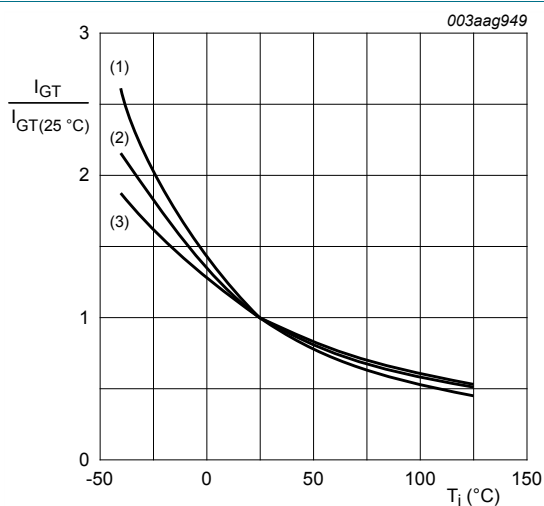
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	10	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	30	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	40	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	30	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	-	20	mA
$V_T$	on-state voltage	$I_T = 6\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	-	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>	-	0.8	1	V
		$V_D = 400\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 125\text{ °C}$ ; <a href="#">Fig. 12</a>	0.2	0.45	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_j = 25\text{ °C}$	-	-	10	$\mu\text{A}$
		$V_D = 800\text{ V}$ ; $T_j = 125\text{ °C}$	-	-	0.5	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25\text{ °C}$	850	-	-	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 13</a>	500	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	4	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	5	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	8	-	-	A/ms



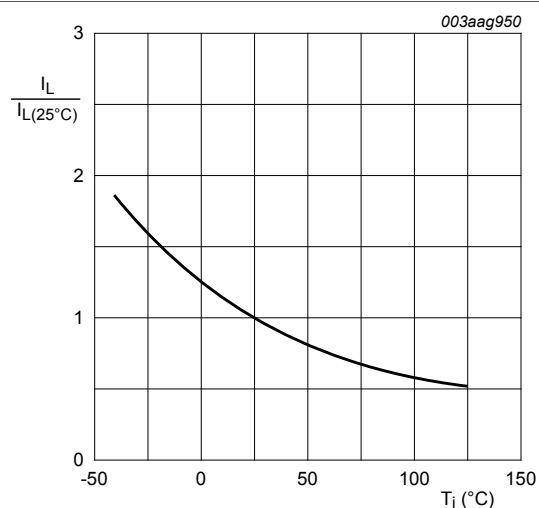
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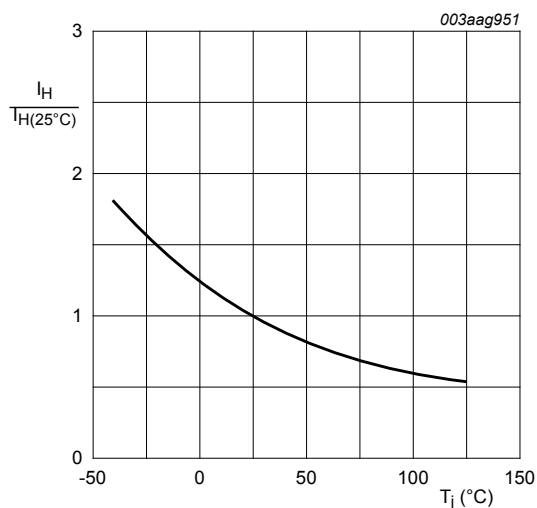
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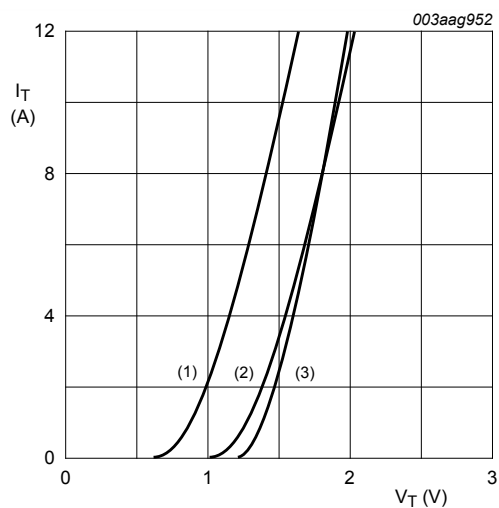
**Fig. 8. Normalized gate trigger current as a function of junction temperature**



**Fig. 9. Normalized latching current as a function of junction temperature**



**Fig. 10. Normalized holding current as a function of junction temperature**



$V_o = 1.242 \text{ V}$ ;  $R_s = 0.074 \Omega$

(1)  $T_j = 125^\circ\text{C}$ ; typical values

(2)  $T_j = 125^\circ\text{C}$ ; maximum values

(3)  $T_j = 25^\circ\text{C}$ ; maximum values

**Fig. 11. On-state current as a function of on-state voltage**

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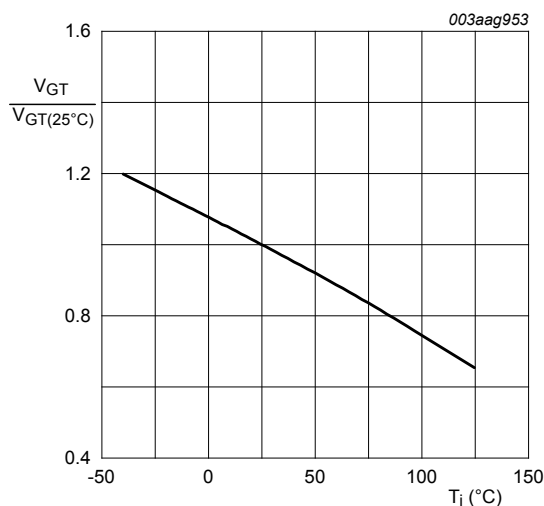
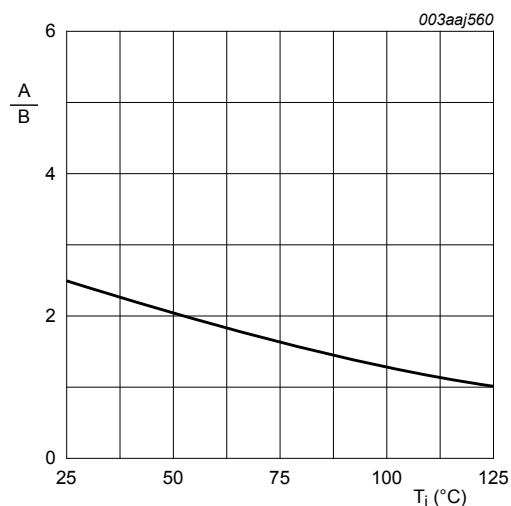
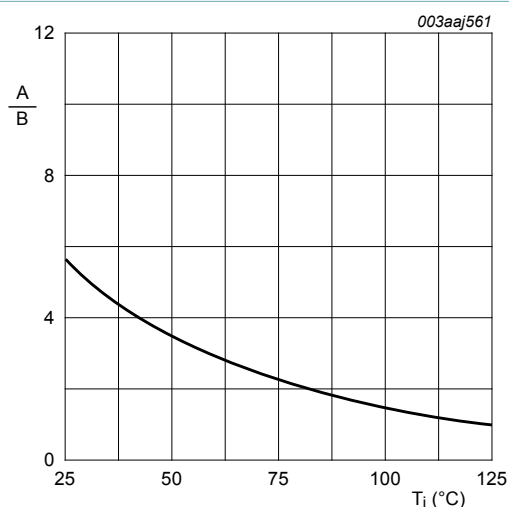


Fig. 12. Normalized gate trigger voltage as a function of junction temperature



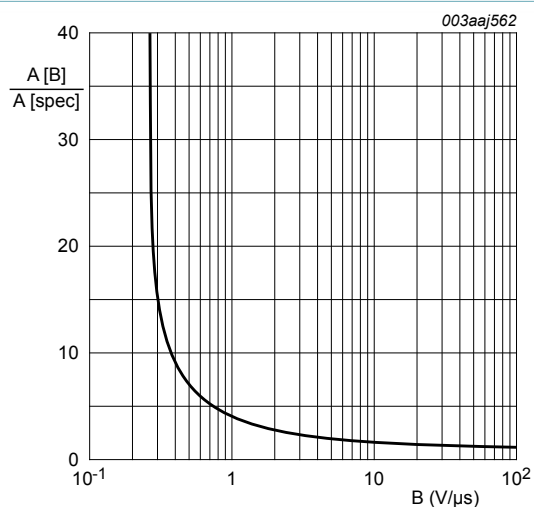
A =  $dV_D/dt$  at condition  $T_j$  °C  
B =  $dV_D/dt$  at condition  $T_j$  [125] °C

Fig. 13. Normalized rate of rise of off-state voltage as a function of junction temperature



A =  $di_{com}/dt$  at condition  $T_j$  °C  
B =  $di_{com}/dt$  at condition  $T_j$  [125] °C  
 $V_D = 400$  V

Fig. 14. Normalized critical rate of rise of commutating current as a function of junction temperature



A [B] is  $di_{com}/dt$  at condition B,  $dV_{com}/dt$   
A [spec] is the specified data sheet value of  $di_{com}/dt$   
turn-off time < 20 ms

Fig. 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

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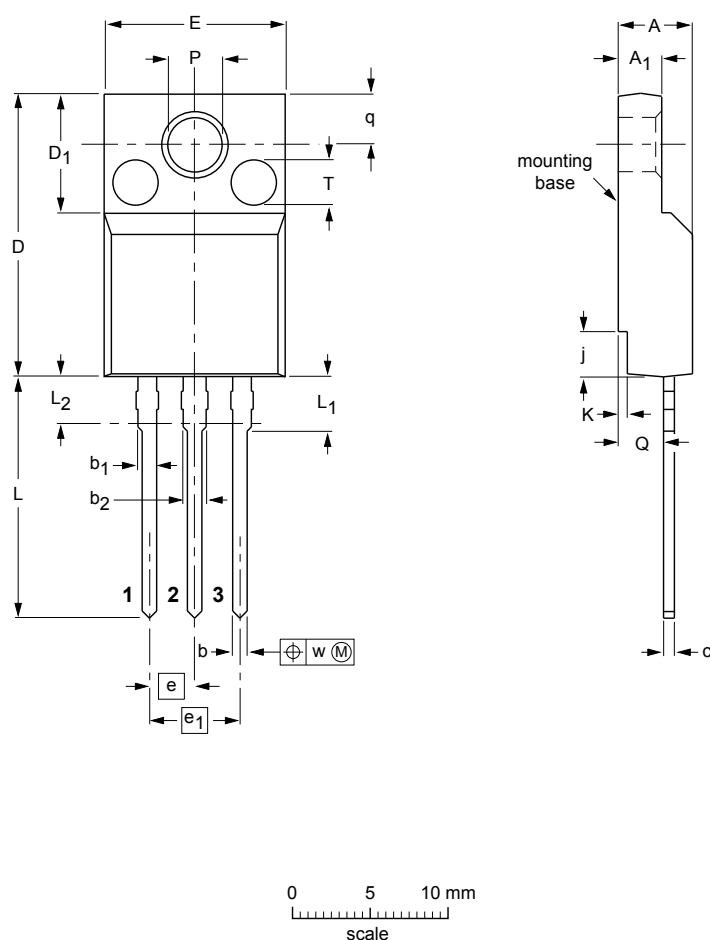
## ACTT4X-800E

AC Thyristor Triac power switch

### 11. Package outline

Plastic single-ended package; isolated heatsink mounted;  
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D	D <sub>1</sub>	E	e	e <sub>1</sub>	j	K	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	P	Q	q	T <sup>(2)</sup>	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

#### Notes

- Terminal dimensions within this zone are uncontrolled.
- Both recesses are # 2.5 × 0.8 max. depth

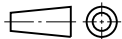
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT186A		3-lead TO-220F				02-04-09 06-02-14

Fig. 16. Package outline TO-220F (SOT186A)

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## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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